In the Claims:

Please cancel claims 5-10 and 12, without prejudice or disclaimer.

Please amend claims 1 and 2, as follows:

1. (Amended) A method of forming a metal gate in a semiconductor device comprising the steps of:

providing a silicon substrate having one or more device isolation films of a trench shape for defining an active region;

forming a gate insulating film on the surface of said silicon substrate by means of a thermal oxidization process;

sequentially forming a barrier metal film and a metal film for a gate on said gate insulating film; and

patterning said metal film for the gate, said barrier metal film, and said gate insulating film,

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wherein deposition of said barrier metal film and said metal film for the gate is performed by a process selected from a group consisting of an atomic layer deposition (ALD) process, a remote plasma chemical vapor deposition process, and a combination thereof.

2. (Amended) The method of forming a metal gate in a semiconductor device according to claim 1, wherein said thermal oxidization process is performed at a temperature in the range of 650°C through 900°C by means of wet ($H_2/O_2$) or dry ($O_2$) method.

**REMARKS**

Claims 5-10 and 12 have been canceled; claims 1-4, 11 and 13-14 are pending in the present application.

A certified translation of the Korean priority application no. 2000-85582, filed on December 29, 2000 is submitted herewith thereby perfecting the priority claim of this application.

The drawings have been objected to under rule 83(a). In response, claim 12 has been canceled and applicants respectfully submit that the rest of the objections set forth on paragraph no. 6, page 3 of the office action do not make sense. Specifically, referring to the objection of claim 1 which recites a